

ABSTRACT OF THE DISCLOSURE

There are disclosed a production apparatus for producing a gallium nitride film semiconductor by HVPE process, a cleaning apparatus for cleaning exhaust gas coming from the above apparatus and an overall production plant for producing a gallium nitride film semiconductor by HVPE process. Therein exhaust piping for exhaust gas in the production apparatus, introduction piping for the cleaning apparatus and exhaust gas piping which connects the production apparatus and the cleaning apparatus are each composed of an electroconductive corrosion-resistant material and are each electrically grounded, thereby surely preventing electrostatic charging due to friction between ammonium chloride powders in the exhaust gas and inside walls of exhaust gas piping, and markedly enhancing operational safety.

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